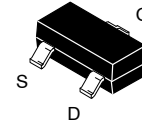


Switch, N-Channel

MMBF4117



SOT-23 (TO-236)
CASE 318-08

Note: Source & Drain are interchangeable.

Description

This device is designed for low current DC and audio applications. These devices provide excellent performance as input stages for sub-picoamp instrumentation or any high impedance signal sources. Sourced from process 53.

ABSOLUTE MAXIMUM RATINGS

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{DG}	Drain-Gate Voltage	40	V
V_{GS}	Gate-Source Voltage	-40	V
I_{GF}	Forward Gate Current	50	mA
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are based on a maximum junction temperature of 150°C .
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.

THERMAL CHARACTERISTICS

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Total Device Dissipation	225	mW
	Derate Above 25°C	1.8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	556	$^\circ\text{C}/\text{W}$

- Device mounted on FR-4 PCB 1.6 inch x 1.6 inch x 0.06 inch.

ELECTRICAL CHARACTERISTICS

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min	Max	Unit
--------	-----------	------------	-----	-----	------

OFF CHARACTERISTICS

$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	$I_G = -1.0 \mu\text{A}, V_{DS} = 0$	-40	-	V
I_{GSS}	Gate Reverse Current	$V_{GS} = -20 \text{ V}, V_{DS} = 0$	-	-10	pA
		$V_{GS} = -20 \text{ V}, V_{DS} = 0, T_A = 150^\circ\text{C}$	-	-25	nA
$V_{GS(off)}$	Gate-Source Cut-Off Voltage	$V_{DS} = -10 \text{ V}, I_D = 1.0 \text{ nA}$	-0.6	-1.8	V

ON CHARACTERISTICS

I_{DSS}	Zero-Gate Voltage Drain Current	$V_{DS} = 10 \text{ V}, V_{GS} = 0$	30	90	μA
-----------	---------------------------------	-------------------------------------	----	----	---------------

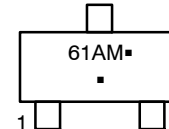
SMALL SIGNAL CHARACTERISTICS

g_{fs}	Common Source Forward Transconductance	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$	70	210	μmhos
g_{oss}	Common-Source Output Conductance	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$	-	3.0	μmhos
$R_{e(yfs)}$	Common-Source Forward Transconductance	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 30 \text{ MHz}$	60	-	μmhos
C_{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$	-	3.0	pF
C_{rss}	Reverse Transfer Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$	-	1.5	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Pulse test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 1.0\%$.

MARKING DIAGRAM



61A = Specific Device Code
M = Date Code
▪ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBF4117	SOT-23 3L	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

TYPICAL CHARACTERISTICS

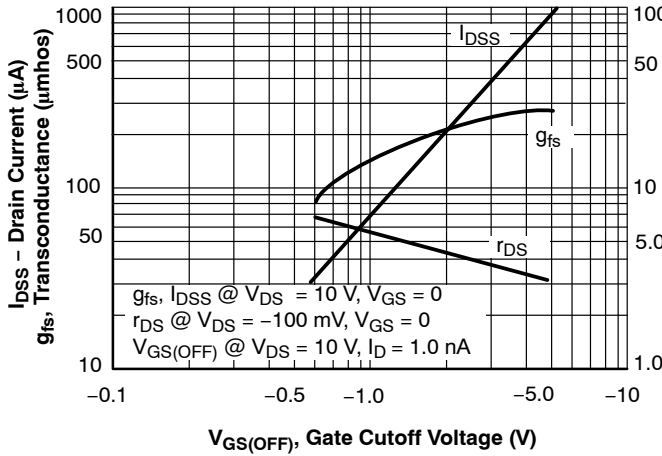


Figure 1. Parameter Interactions

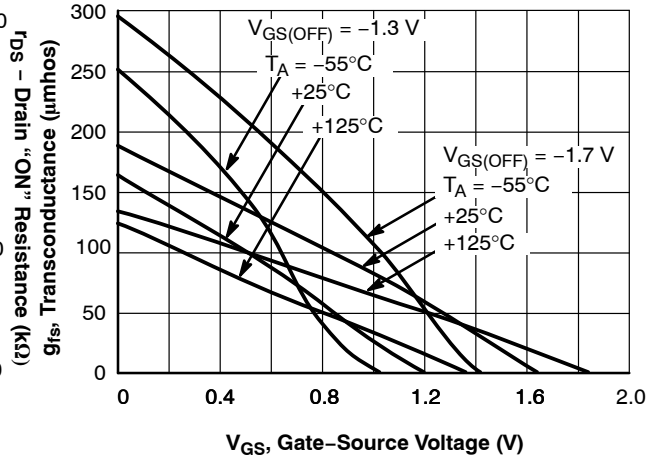


Figure 2. Transfer Characteristics

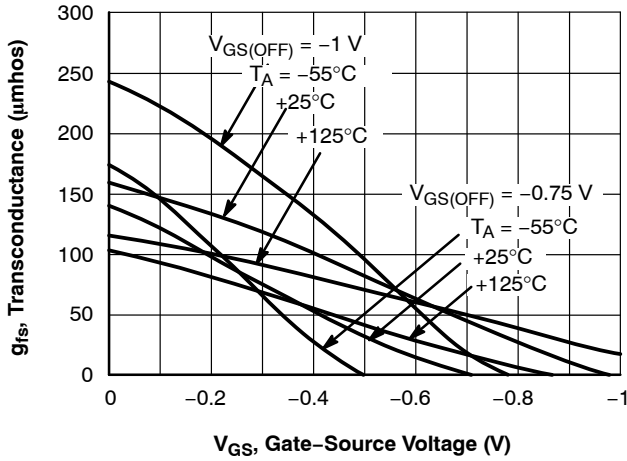


Figure 3. Transfer Characteristics

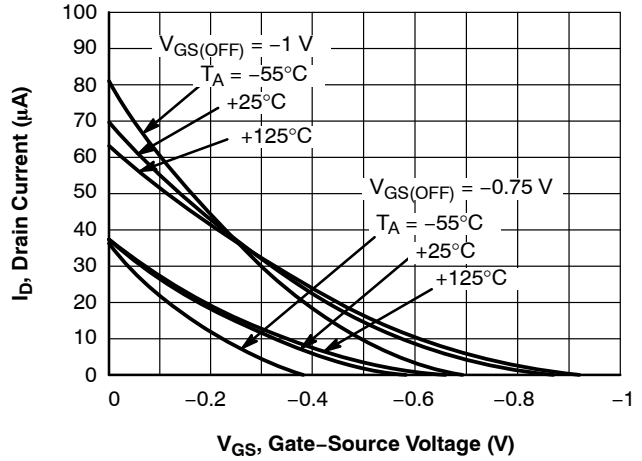


Figure 4. Transfer Characteristics

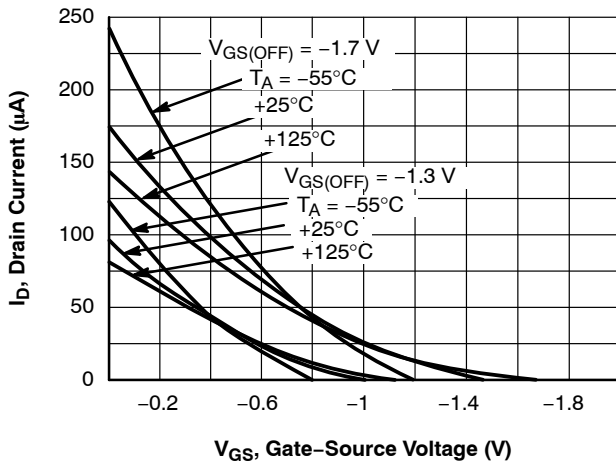


Figure 5. Transfer Characteristics

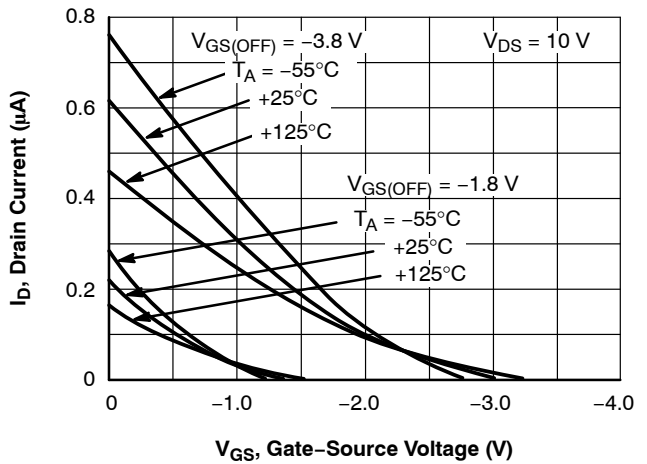


Figure 6. Transfer Characteristics

TYPICAL CHARACTERISTICS (Continued)

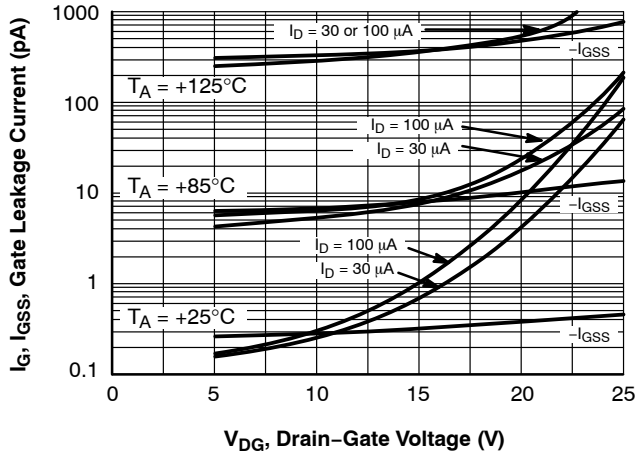


Figure 7. Leakage Current vs. Voltage

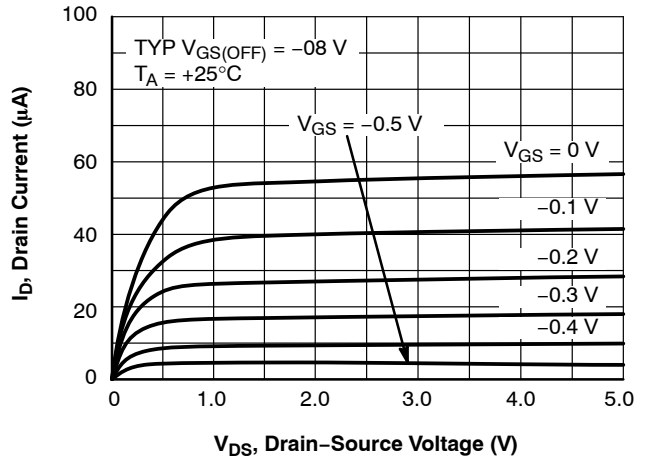


Figure 8. Common Drain-Source

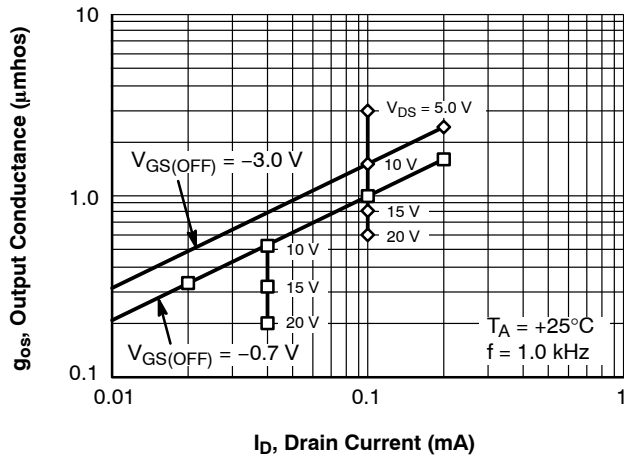


Figure 9. Output Conductance vs. Drain Current

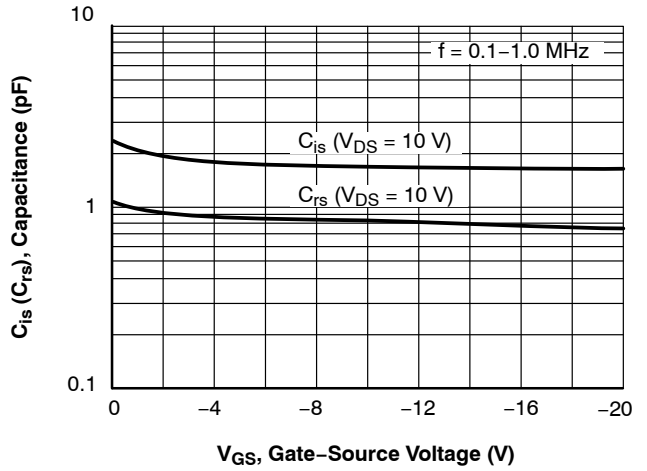


Figure 10. Capacitance vs. Voltage

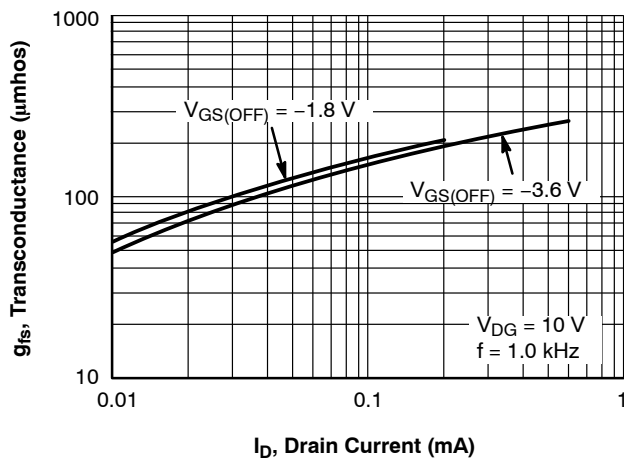


Figure 11. Transconductance vs. Drain Current

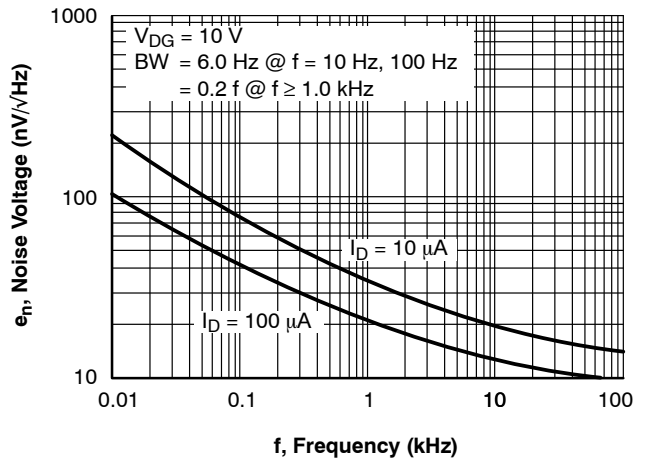


Figure 12. Noise Voltage vs. Frequency

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H _E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**



**SOT-23 (TO-236)
CASE 318
ISSUE AT**

DATE 01 MAR 2023

- | | | | | | |
|---|---|---|---|---|---|
| STYLE 1 THRU 5:
CANCELLED | STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE | | |
| STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE | STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE | STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE |
| STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE | STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE | STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE | STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE | STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE | STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE |
| STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT | STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE | STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE | STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION |
| STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE | STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE | | | | |

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